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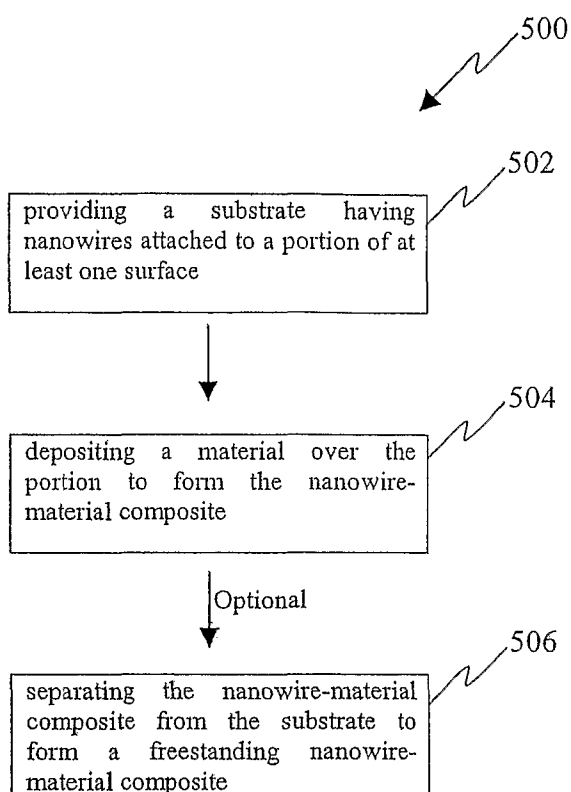
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(54) Title: SYSTEM AND PROCESS FOR PRODUCING NANOWIRE COMPOSITES AND ELECTRONIC SUBSTRATES THEREFROM



(57) Abstract: The present invention relates to a system and process for producing a nanowire-material composite. A substrate having nanowires attached to a portion of at least one surface is provided. A material is deposited over the portion to form the nanowire-material composite. The process further optionally comprises separating the nanowire-material composite from the substrate to form a freestanding nanowire-material composite. The freestanding nanowire material composite is optionally further processed into an electronic substrate. A variety of electronic substrates can be produced using the methods described herein. For example, a multi-color light-emitting diode can be produced from multiple, stacked layers of nanowire-material composites, each composite layer emitting light at a different wavelength.

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